

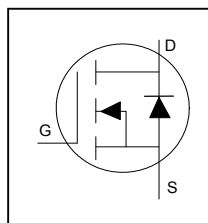
Application

- Brushed motor drive applications
- BLDC motor drive applications
- Battery powered circuits
- Half-bridge and full-bridge topologies
- Synchronous rectifier applications
- Resonant mode power supplies
- OR-ing and redundant power switches
- DC/DC and AC/DC converters
- DC/AC inverters

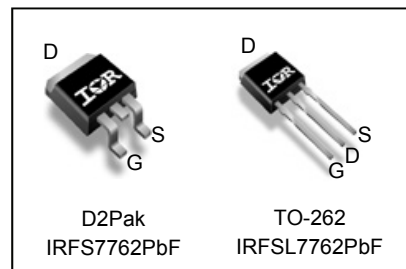
Benefits

- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche SOA
- Enhanced body diode dV/dt and dI/dt capability
- Lead-free, RoHS compliant

HEXFET® Power MOSFET



V_{DS}	75V
$R_{DS(on)}$ typ. max	5.6mΩ
	6.7mΩ
I_D	85A



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFSL7762PbF	TO-262	Tube	50	IRFSL7762PbF
IRFS7762PbF	D ² -Pak	Tube	50	IRFS7762PbF
		Tape and Reel Left	800	IRFS7762TRLpbf

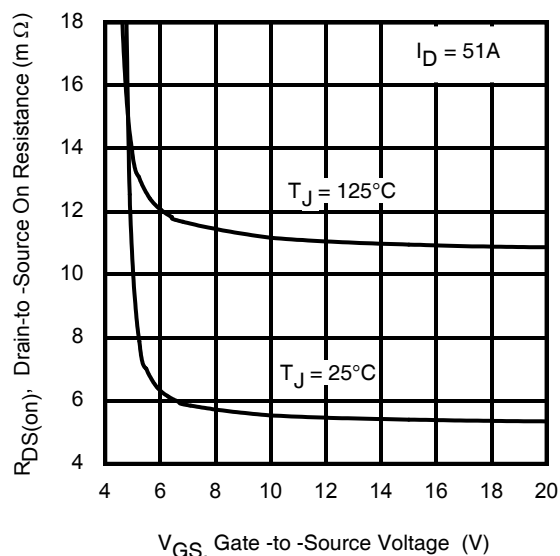


Fig 1. Typical On-Resistance vs. Gate Voltage

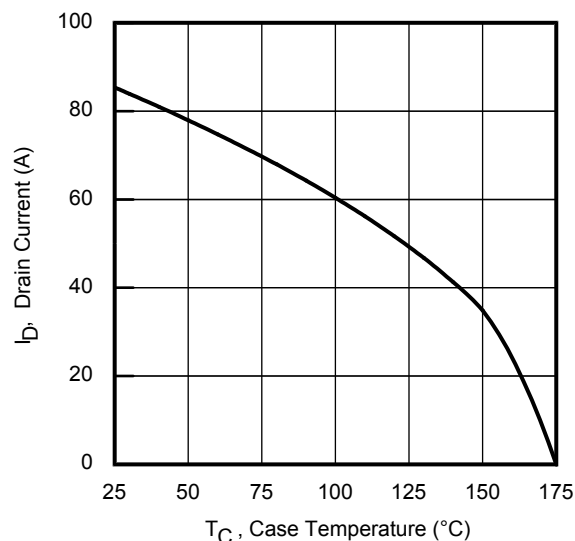


Fig 2. Maximum Drain Current vs. Case Temperature

Absolute Maximum Rating

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	85	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	60	
I_{DM}	Pulsed Drain Current ①	335	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	140	W
	Linear Derating Factor	0.95	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Avalanche Characteristics

Symbol	Parameter	Max.	Units
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ③	160	mJ
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ⑧	243	
I_{AR}	Avalanche Current ①	See Fig 15, 16, 23a, 23b	A
E_{AR}	Repetitive Avalanche Energy ①		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑦	—	1.05	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑨	—	40	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	75	—	—	V	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	58	—	mV/°C	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	5.6	6.7	mΩ	$V_{GS} = 10\text{V}$, $I_D = 51\text{A}$
		—	6.6	—		$V_{GS} = 6.0\text{V}$, $I_D = 26\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	2.1	—	3.7	V	$V_{DS} = V_{GS}$, $I_D = 100\mu\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 75\text{V}$, $V_{GS} = 0\text{V}$
		—	—	150		$V_{DS} = 75\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20\text{V}$
R_G	Gate Resistance	—	2.5	—	Ω	

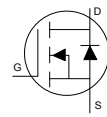
Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 120\mu\text{H}$, $R_G = 50\Omega$, $I_{AS} = 51\text{A}$, $V_{GS} = 10\text{V}$.
- ③ $I_{SD} \leq 51\text{A}$, $di/dt \leq 735\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ R_θ is measured at T_J approximately 90°C .
- ⑧ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 1\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 22\text{A}$, $V_{GS} = 10\text{V}$.
- ⑨ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994: <http://www.irf.com/technical-info/appnotes/an-994.pdf>

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	180	—	—	S	$V_{DS} = 10\text{V}$, $I_D = 51\text{A}$
Q_g	Total Gate Charge	—	85	130	nC	$I_D = 51\text{A}$ $V_{DS} = 38\text{V}$ $V_{GS} = 10\text{V}$
Q_{gs}	Gate-to-Source Charge	—	21	—		
Q_{gd}	Gate-to-Drain Charge	—	26	—		
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	60	—		
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$V_{DD} = 38\text{V}$ $I_D = 51\text{A}$ $R_G = 2.7\Omega$ $V_{GS} = 10\text{V}$ ④
t_r	Rise Time	—	49	—		
$t_{d(off)}$	Turn-Off Delay Time	—	57	—		
t_f	Fall Time	—	40	—		
C_{iss}	Input Capacitance	—	4440	—	pF	$V_{GS} = 0\text{V}$
C_{oss}	Output Capacitance	—	370	—		$V_{DS} = 25\text{V}$
C_{rss}	Reverse Transfer Capacitance	—	230	—		$f = 1.0\text{MHz}$, See Fig.7
$C_{oss\text{ eff.}(ER)}$	Effective Output Capacitance (Energy Related)	—	330	—		$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$ to 60V ⑥
$C_{oss\text{ eff.}(TR)}$	Output Capacitance (Time Related)	—	430	—		$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$ to 60V ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	85	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	335		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}$, $I_S = 51\text{A}$, $V_{GS} = 0\text{V}$ ④
dv/dt	Peak Diode Recovery dv/dt	—	13	—	V/ns	$T_J = 175^\circ\text{C}$, $I_S = 51\text{A}$, $V_{DS} = 75\text{V}$ ③
t_{rr}	Reverse Recovery Time	—	34	—	ns	$T_J = 25^\circ\text{C}$ $V_{DD} = 64\text{V}$
		—	46	—		$T_J = 125^\circ\text{C}$ $I_F = 51\text{A}$,
Q_{rr}	Reverse Recovery Charge	—	54	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100\text{A}/\mu\text{s}$ ④
		—	69	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	2.7	—	A	$T_J = 25^\circ\text{C}$

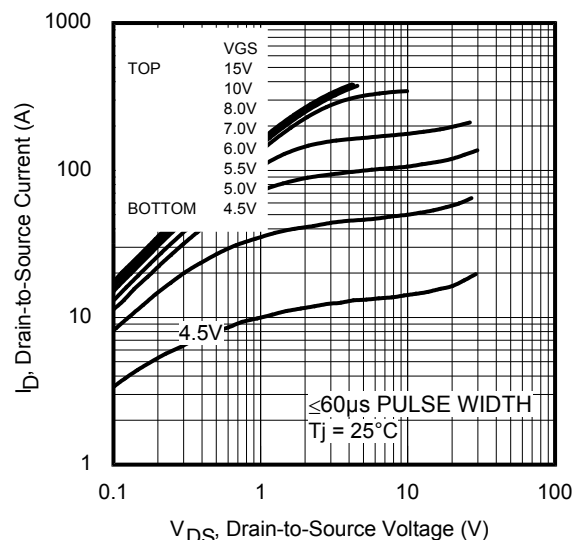


Fig 3. Typical Output Characteristics

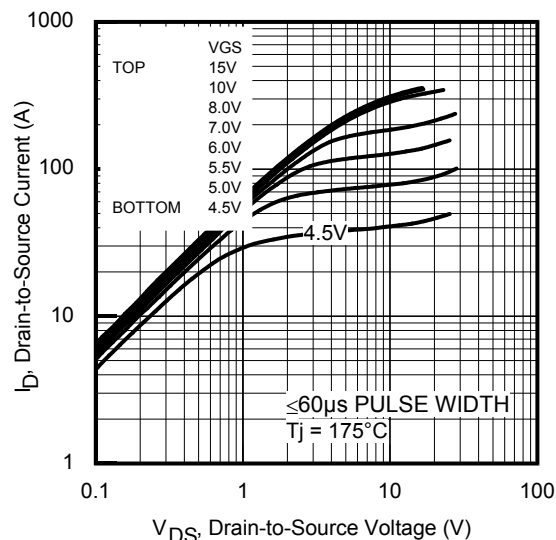


Fig 4. Typical Output Characteristics

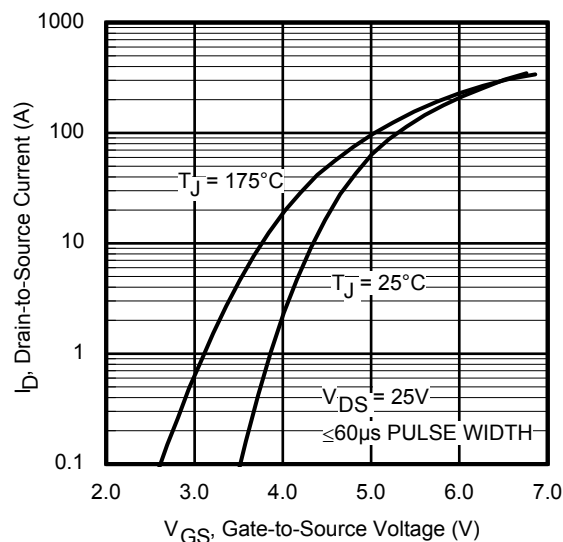


Fig 5. Typical Transfer Characteristics

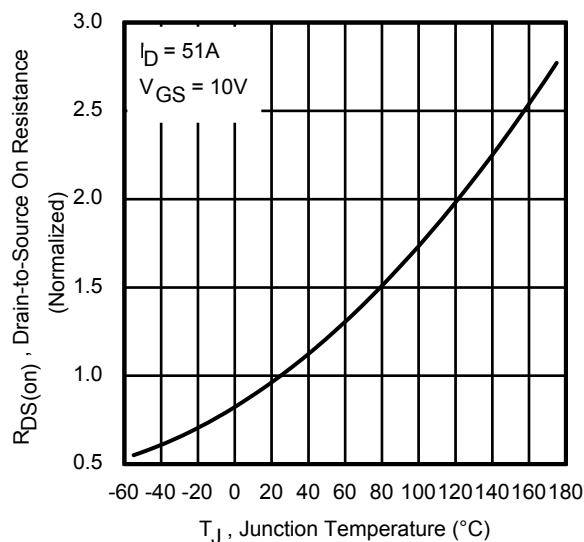


Fig 6. Normalized On-Resistance vs. Temperature

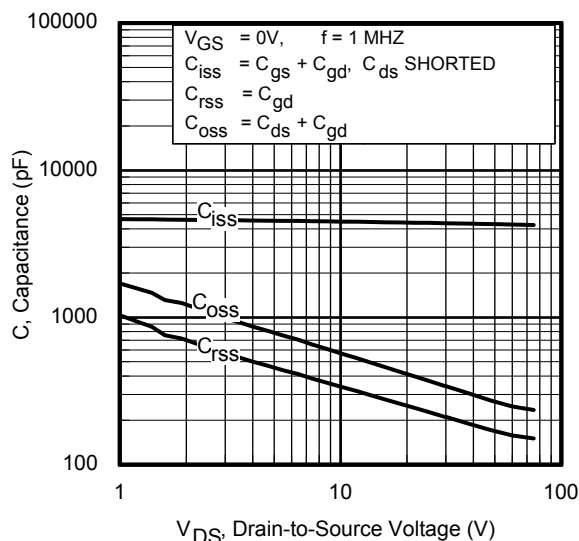


Fig 7. Typical Capacitance vs. Drain-to-Source Voltage

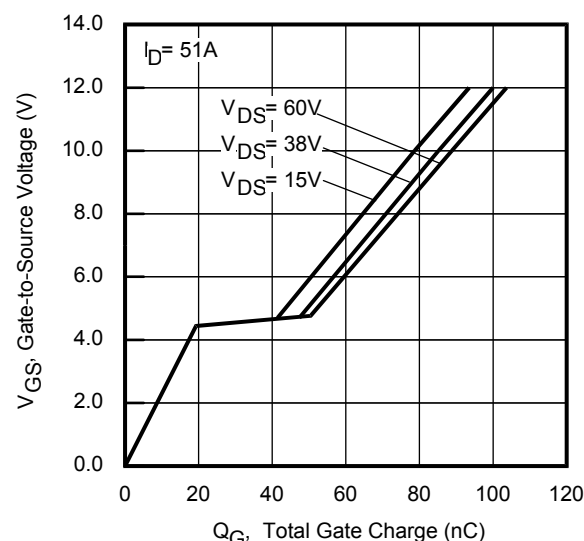
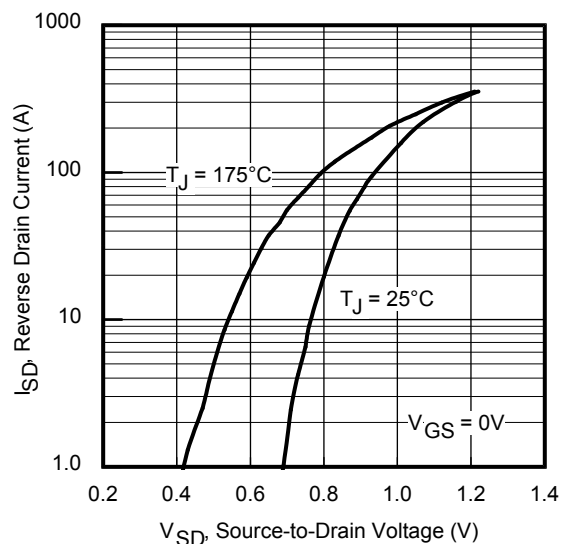
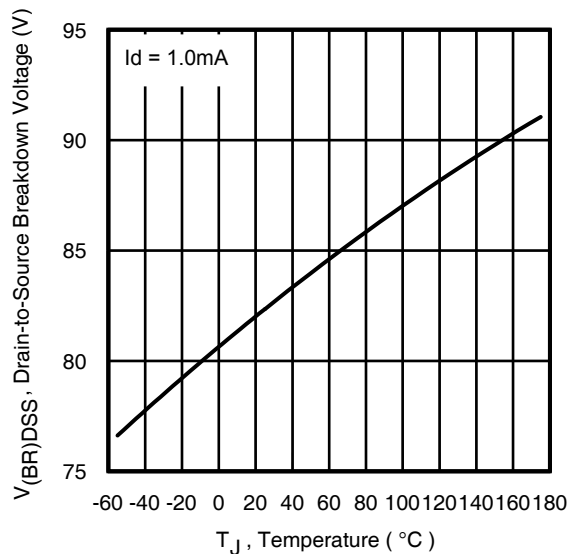
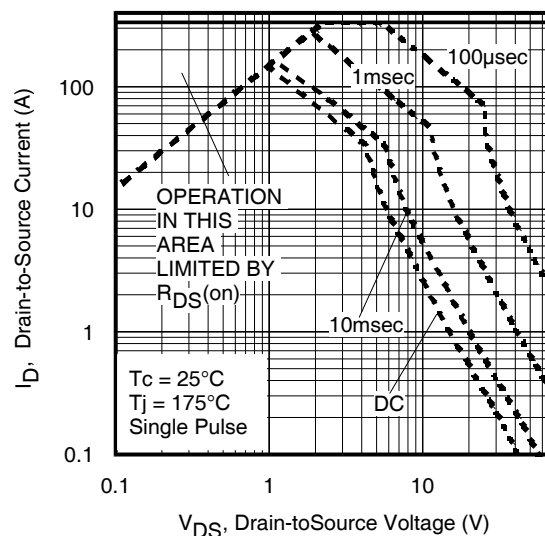
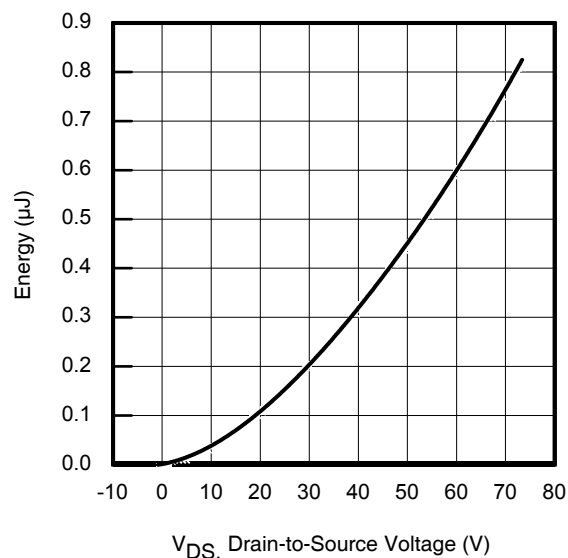
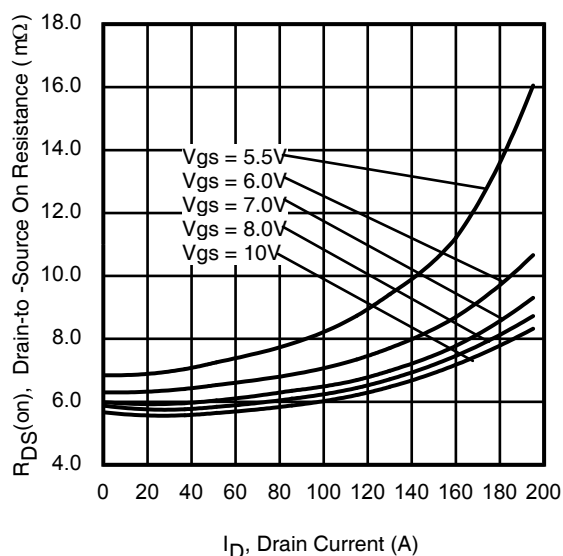


Fig 8. Typical Gate Charge vs. Gate-to-Source Voltage


Fig 9. Typical Source-Drain Diode Forward Voltage

Fig 11. Drain-to-Source Breakdown Voltage

Fig 10. Maximum Safe Operating Area

Fig 12. Typical C_{oss} Stored Energy

Fig 13. Typical On-Resistance vs. Drain Current

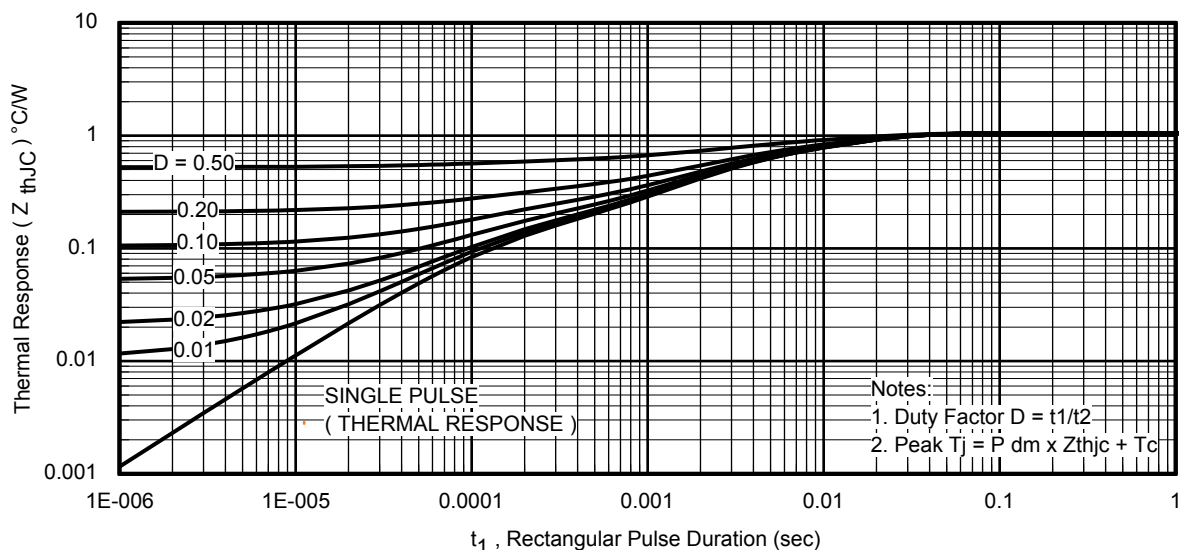


Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Case

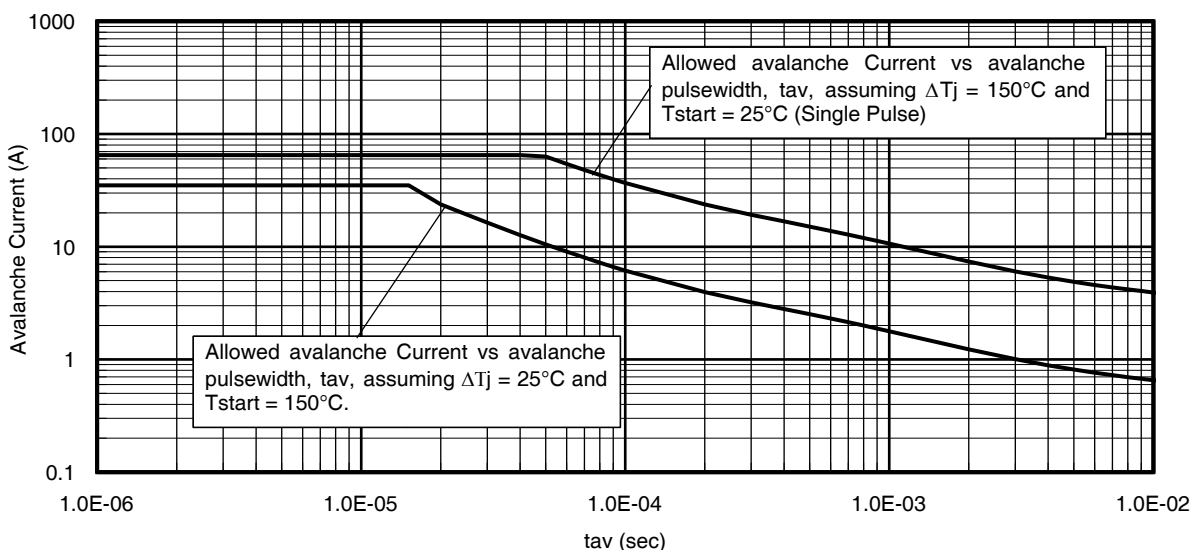


Fig 15. Avalanche Current vs. Pulse Width

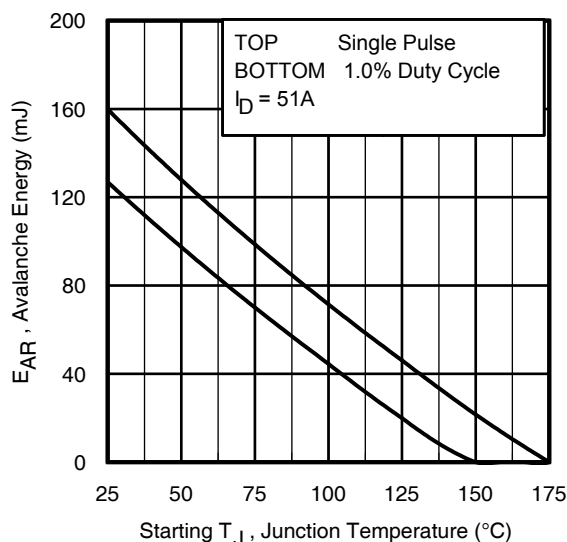
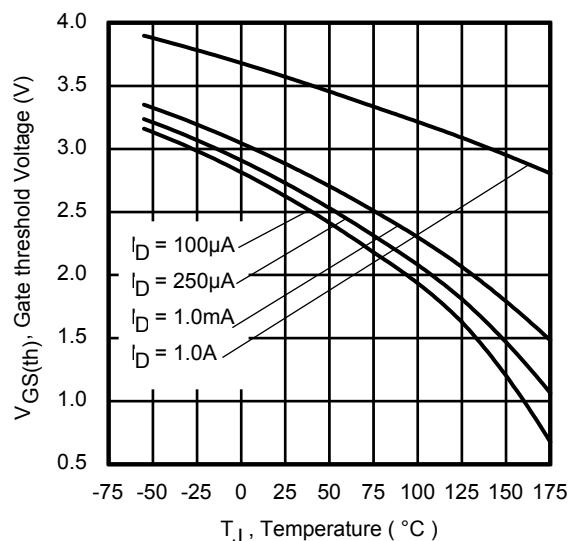
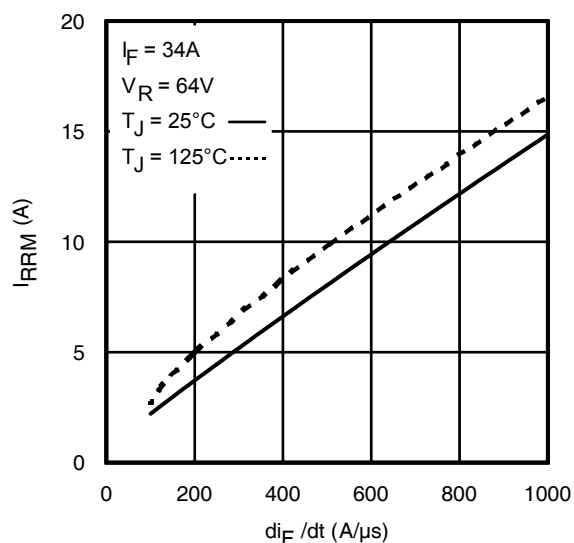
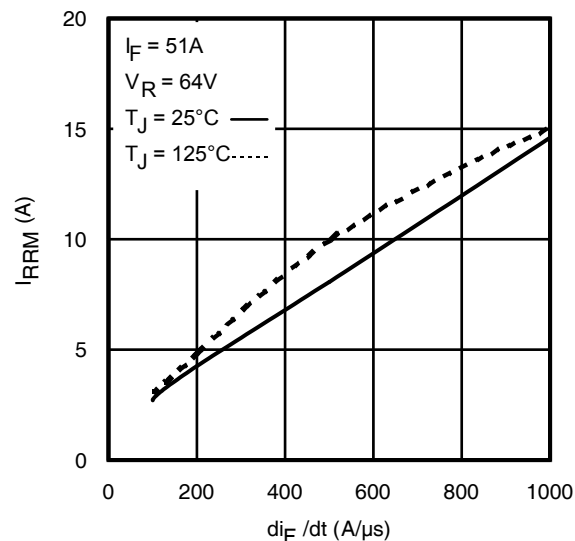
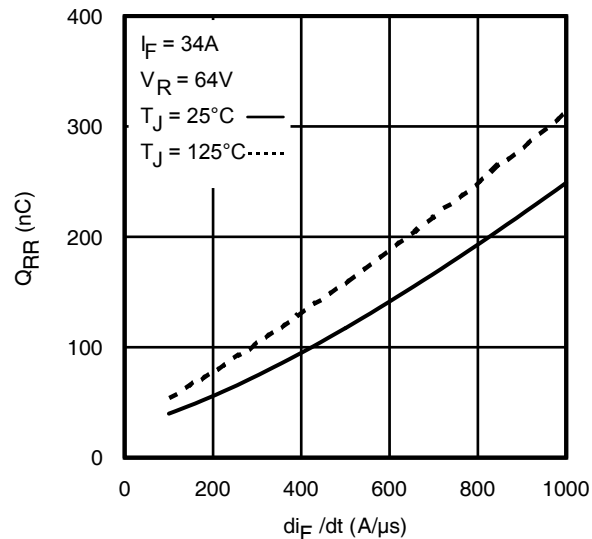
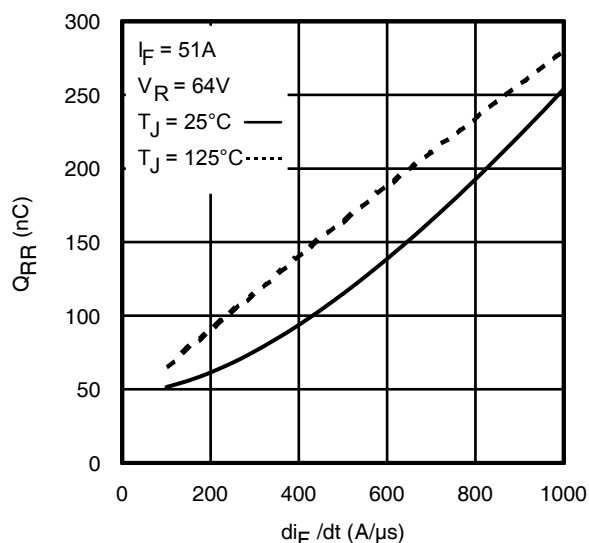


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16: (For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)
 $P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$
 $E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$


Fig 17. Threshold Voltage vs. Temperature

Fig 18. Typical Recovery Current vs. di_F/dt

Fig 19. Typical Recovery Current vs. di_F/dt

Fig 20. Typical Stored Charge vs. di_F/dt

Fig 21. Typical Stored Charge vs. di_F/dt

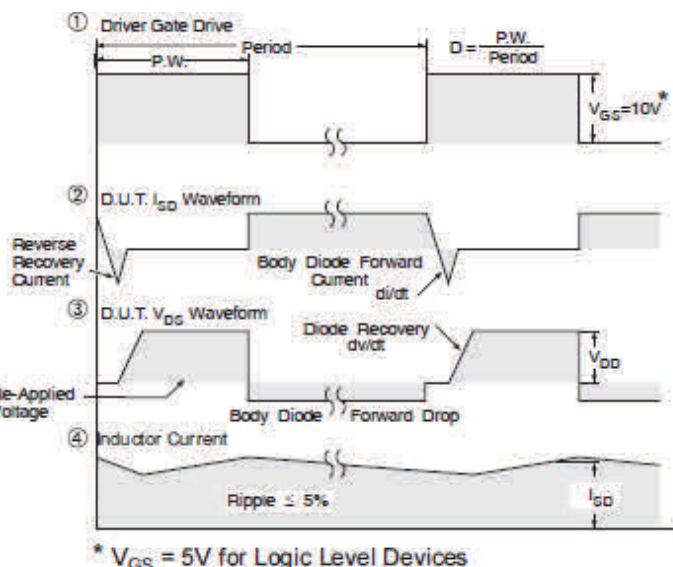
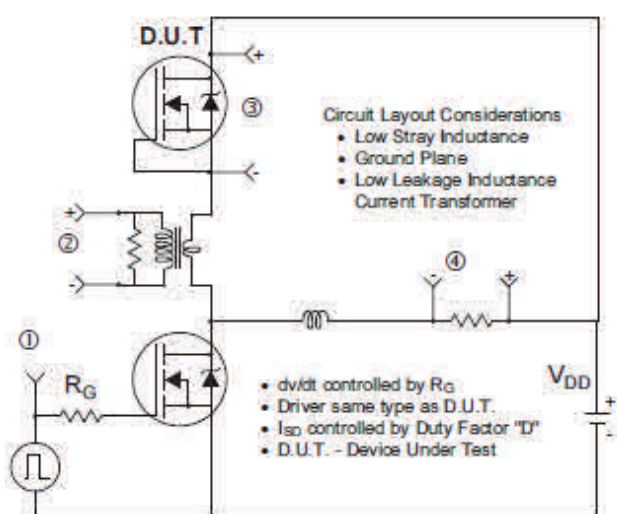


Fig 22. Peak Diode Recovery dV/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

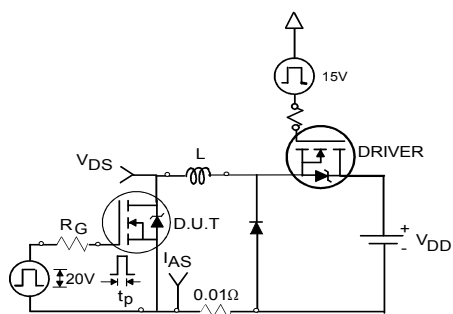


Fig 23a. Unclamped Inductive Test Circuit

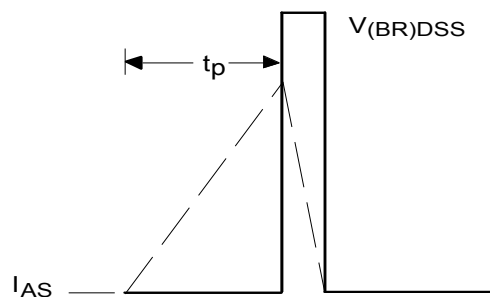


Fig 23b. Unclamped Inductive Waveforms

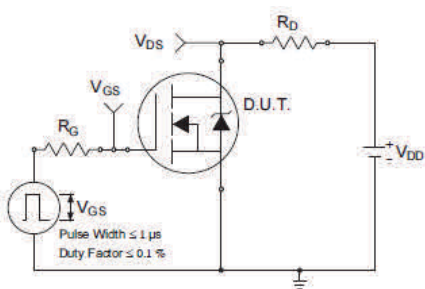


Fig 24a. Switching Time Test Circuit

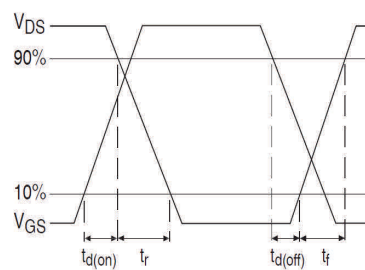


Fig 24b. Switching Time Waveforms

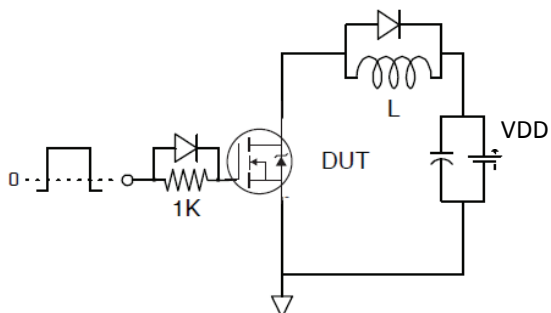


Fig 25a. Gate Charge Test Circuit

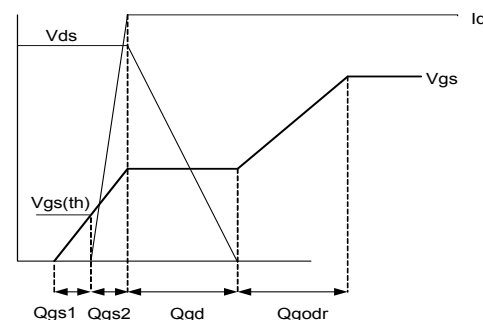
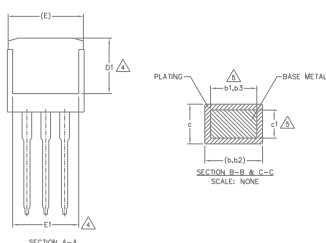
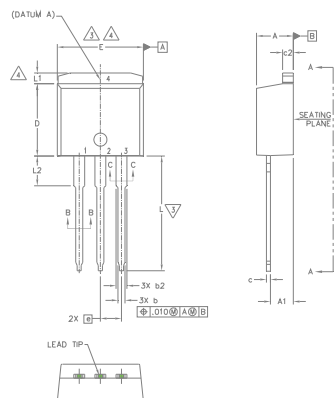


Fig 25b. Gate Charge Waveform

TO-262 Package Outline (Dimensions are shown in millimeters (inches))



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A.1	2.03	3.02	.080	.119	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245	—	4
e	2.54	BSG	.100	BSG	
L	13.46	14.10	.530	.555	
L1	—	1.65	—	.065	4
L2	3.56	3.71	.140	.146	

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION: INCH.
- 7.- OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

LEAD ASSIGNMENTS

- IGBTs, CoPACK
1. – GATE
 2. – COLLECTOR
 3. – EMITTER
 4. – COLLECTOR

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

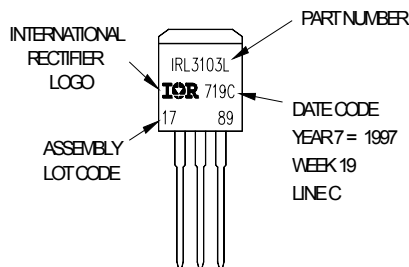
DIODES

- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
- 2, 4.- CATHODE
- 3.- ANODE

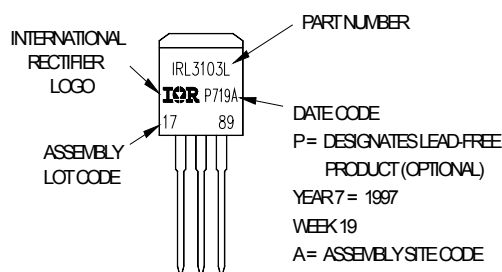
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"

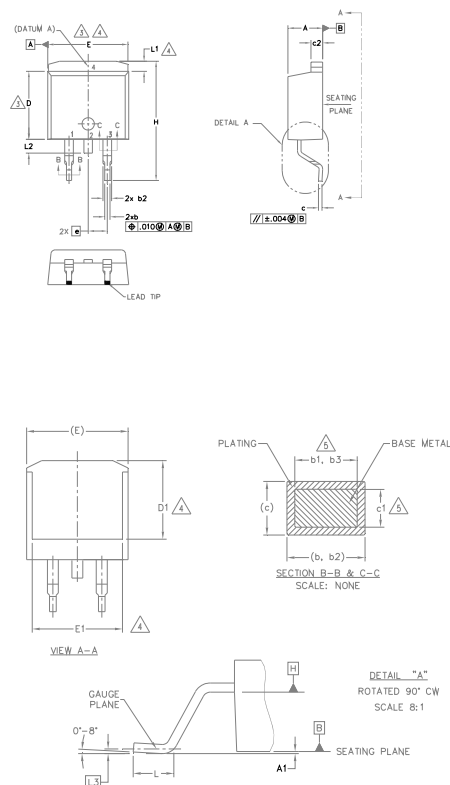


OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D²Pak (TO-263AB) Package Outline (Dimensions are shown in millimeters (inches))



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	5
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	5
c1	0.38	0.58	.015	.023	
c2	1.14	1.65	.045	.065	3
D	8.38	9.65	.330	.380	
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245	—	4
e	2.54 BSC		.100 BSC		4
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	—	1.68	—	.066	
L2	—	1.78	—	.070	
L3	0.25 BSC		.010 BSC		

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1, b3 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

LEAD ASSIGNMENTS

DIODES

- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
- 2, 4.- CATHODE
- 3.- ANODE

HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

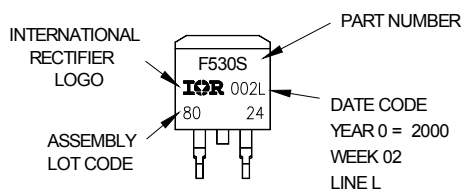
IGBTs, CoPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

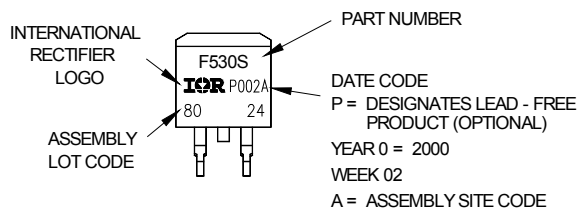
D²Pak (TO-263AB) Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON VVV 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position
indicates "Lead - Free"

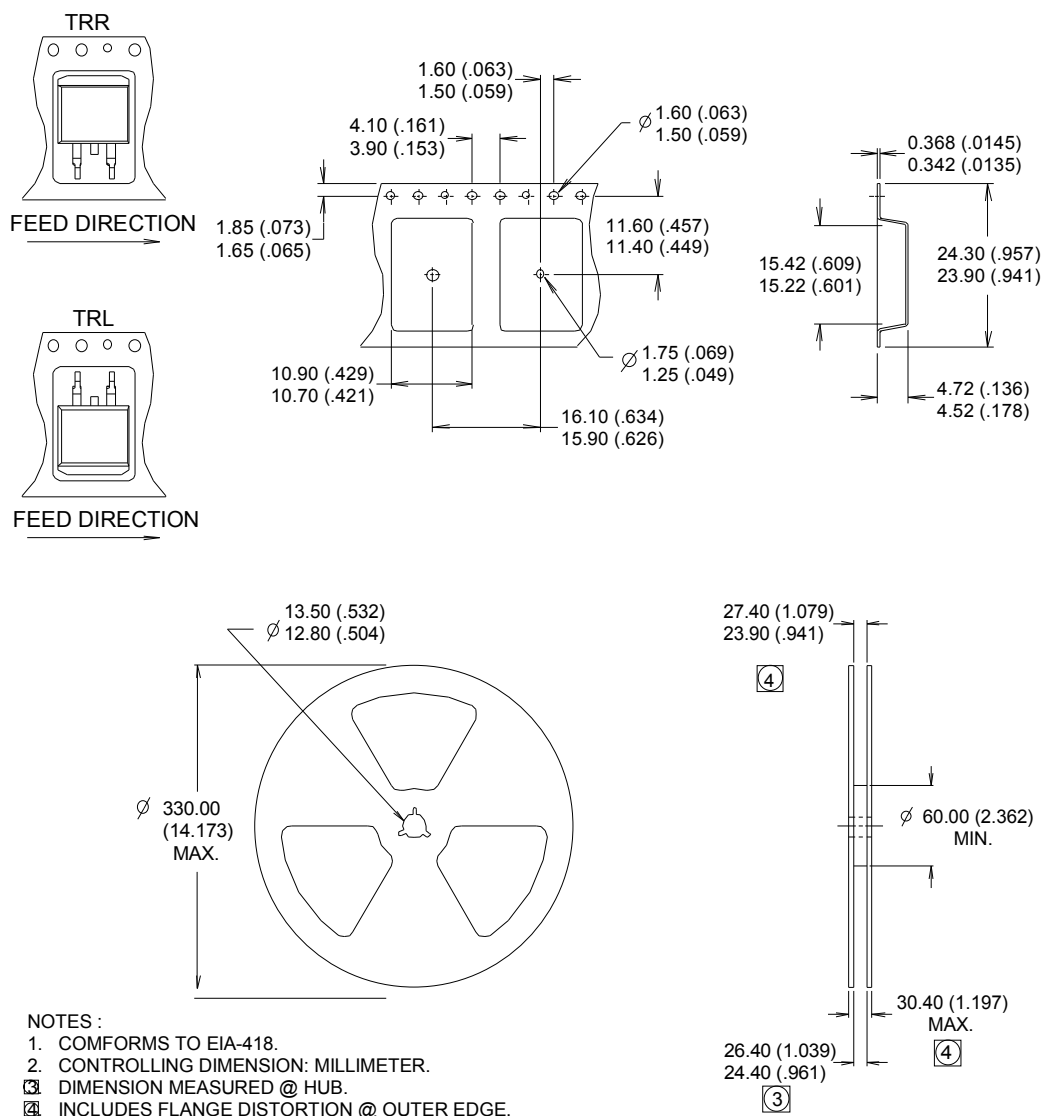


OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D²Pak (TO-263AB) Tape & Reel Information (Dimensions are shown in millimeters (inches))



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level			Industrial (per JEDEC JESD47F) ††	
Moisture Sensitivity Level	D ² Pak		MSL1	
	TO-262			
RoHS Compliant			Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability/>

^{††} Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Comments
2/19/2015	- Updated $E_{AS} (L = 1\text{mH}) = 243\text{mJ}$ on page 2 - Updated note 8 "Limited by $T_{J\text{max}}$, starting $T_J = 25^\circ\text{C}$, $L = 1\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 22\text{A}$, $V_{GS} = 10\text{V}$" on page 2

International
 Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA
 To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>